



## BULD1101ET4

### HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

#### PRELIMINARY DATA

Ordering Code	Marking	Shipment
BULD1101ET4	BULD1101E	Tape & Reel

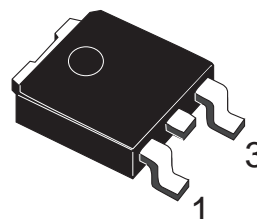
- HIGH VOLTAGE CAPABILITY
- LOW SPREAD OF DYNAMIC PARAMETERS
- MINIMUM LOT-TO-LOT SPREAD FOR RELIABLE OPERATION
- VERY HIGH SWITCHING SPEED
- LARGE RBSOA
- SURFACE-MOUNTING DPAK (TO-252)  
POWER PACKAGE IN TAPE & REEL  
(SUFFIX "T4")

#### APPLICATIONS

- ELECTRONIC BALLASTS FOR  
FLUORESCENT LIGHTING

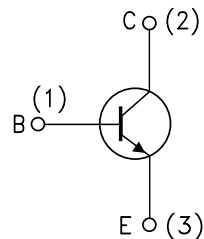
#### DESCRIPTION

The device is manufactured using High Voltage Multi Epitaxial Planar technology for high switching speeds and high voltage capability. It uses a Cellular Emitter structure with planar edge termination to enhance switching speeds while maintaining a wide RBSOA.



**DPAK  
TO-252**  
(Suffix "T4")

#### INTERNAL SCHEMATIC DIAGRAM



SC06960

#### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
$V_{CES}$	Collector-Emitter Voltage ( $V_{BE} = 0$ )	1100	V
$V_{CEO}$	Collector-Emitter Voltage ( $I_B = 0$ )	450	V
$V_{EBO}$	Emitter-Base Voltage ( $I_C = 0$ )	12	V
$I_C$	Collector Current	3	A
$I_{CM}$	Collector Peak Current ( $t_p < 5$ ms)	6	A
$I_B$	Base Current	1.5	A
$I_{BM}$	Base Peak Current ( $t_p < 5$ ms)	3	A
$P_{tot}$	Total Dissipation at $T_c = 25^\circ\text{C}$	35	W
$T_{stg}$	Storage Temperature	-65 to 150	$^\circ\text{C}$
$T_j$	Max. Operating Junction Temperature	150	$^\circ\text{C}$

## BULD1101ET4

### THERMAL DATA

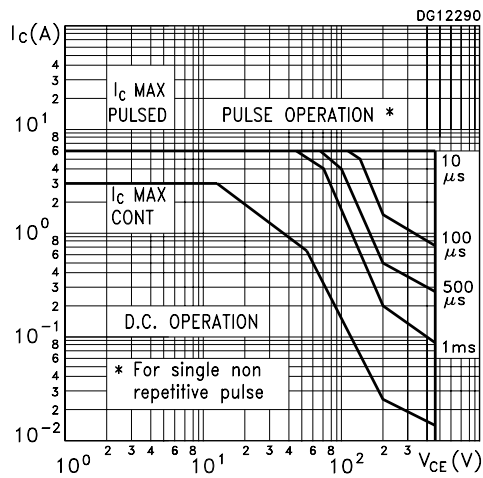
R <sub>thj-case</sub>	Thermal Resistance Junction-Case	Max	3.57	°C/W
R <sub>thj-amb</sub>	Thermal Resistance Junction-ambient	Max	100	°C/W

### ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25 °C unless otherwise specified)

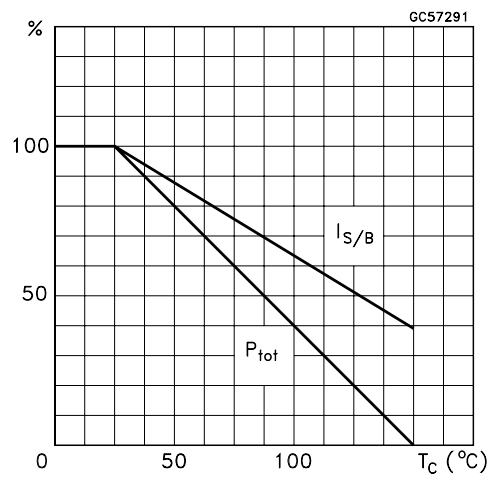
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I <sub>CES</sub>	Collector Cut-off Current (V <sub>BE</sub> = 0)	V <sub>CE</sub> = 1100 V			100	μA
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage (I <sub>C</sub> = 0)	I <sub>E</sub> = 1 mA	12		24	V
V <sub>CEO(sus)*</sub>	Collector-Emitter Sustaining Voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = 100 mA	450			V
V <sub>CE(sat)*</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 1 A I <sub>B</sub> = 200 mA I <sub>C</sub> = 1 A I <sub>B</sub> = 200 mA T <sub>j</sub> = 125°C		0.25 0.6	1 1.5	V V
V <sub>BE(sat)*</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 1 A I <sub>B</sub> = 200 mA			1.5	V
h <sub>FE*</sub>	DC Current Gain	I <sub>C</sub> = 250 mA V <sub>CE</sub> = 5 V I <sub>C</sub> = 250 mA V <sub>CE</sub> = 5 V T <sub>j</sub> = 125°C I <sub>C</sub> = 2 A V <sub>CE</sub> = 5 V I <sub>C</sub> = 2 A V <sub>CE</sub> = 5 V T <sub>j</sub> = 125°C	20 23 6 4	38 44 10 7	80 85 18 16	
t <sub>s</sub> t <sub>f</sub>	RESISTIVE LOAD Storage Time Fall Time	I <sub>C</sub> = 2.5 A V <sub>CC</sub> = 125 V V <sub>BB(off)</sub> = -5 V t <sub>P</sub> = 300 μs I <sub>B1</sub> = -I <sub>B2</sub> = 0.5 A (see figure 1)		400	2 700	μs ns
E <sub>ar</sub>	Repetitive Avalanche Energy	L = 2 mH C = 1.8 nF I <sub>BR</sub> ≤ 2.5 A (see figure 2)	6			mJ

\* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

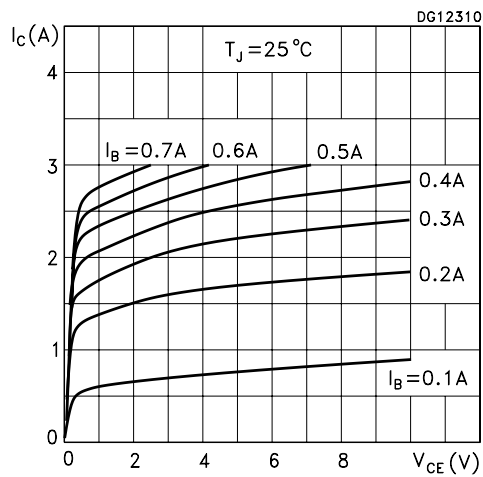
### Safe Operating Area



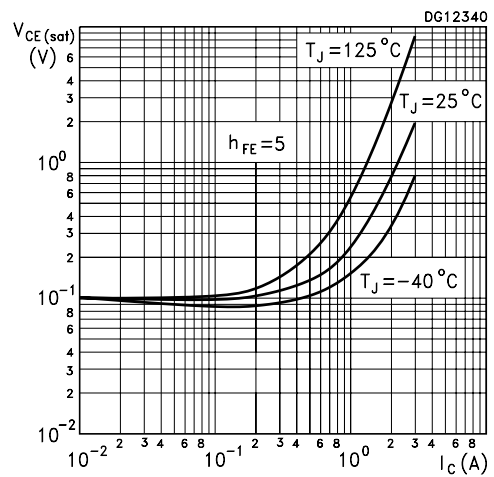
### Derating Curve



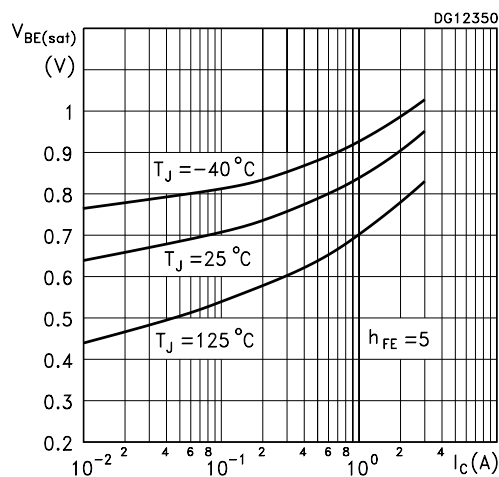
### Output Characteristics



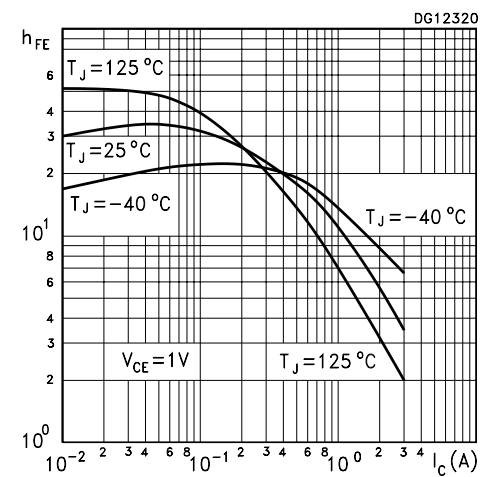
### Collector-Emitter Saturation Voltage



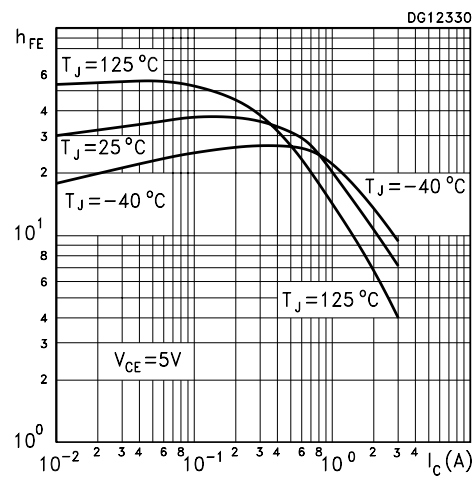
### Base-Emitter Saturation Voltage



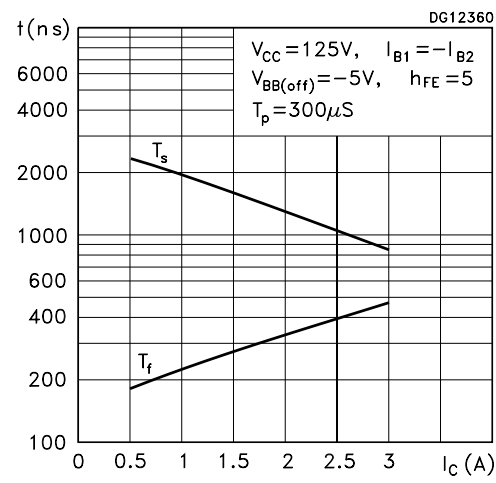
### DC Current Gain



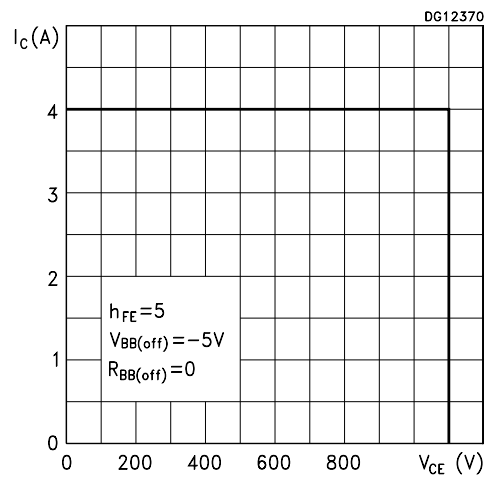
DC Current Gain

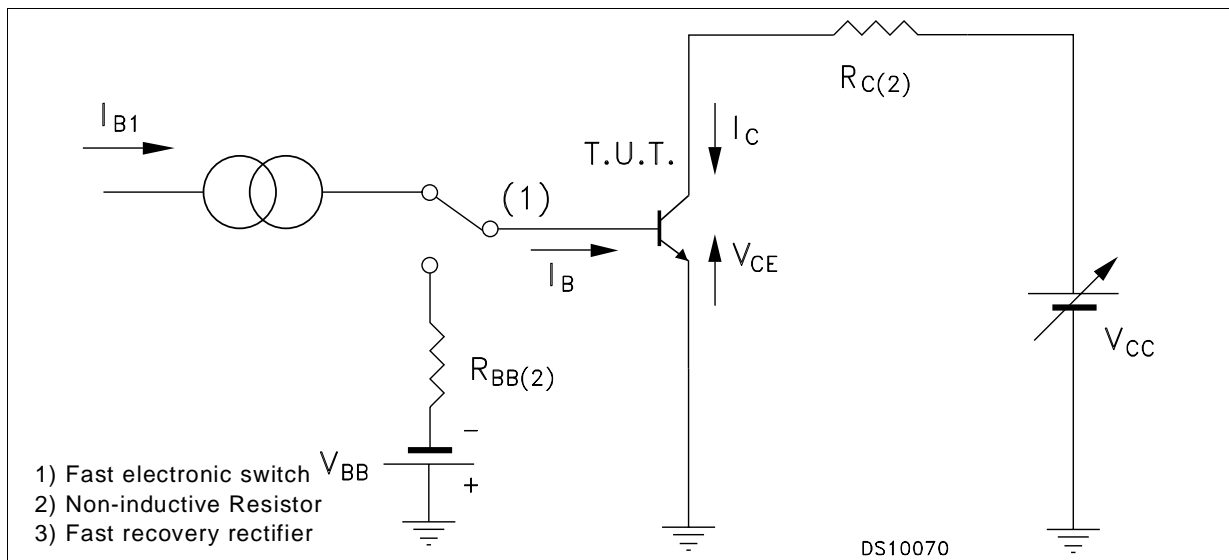
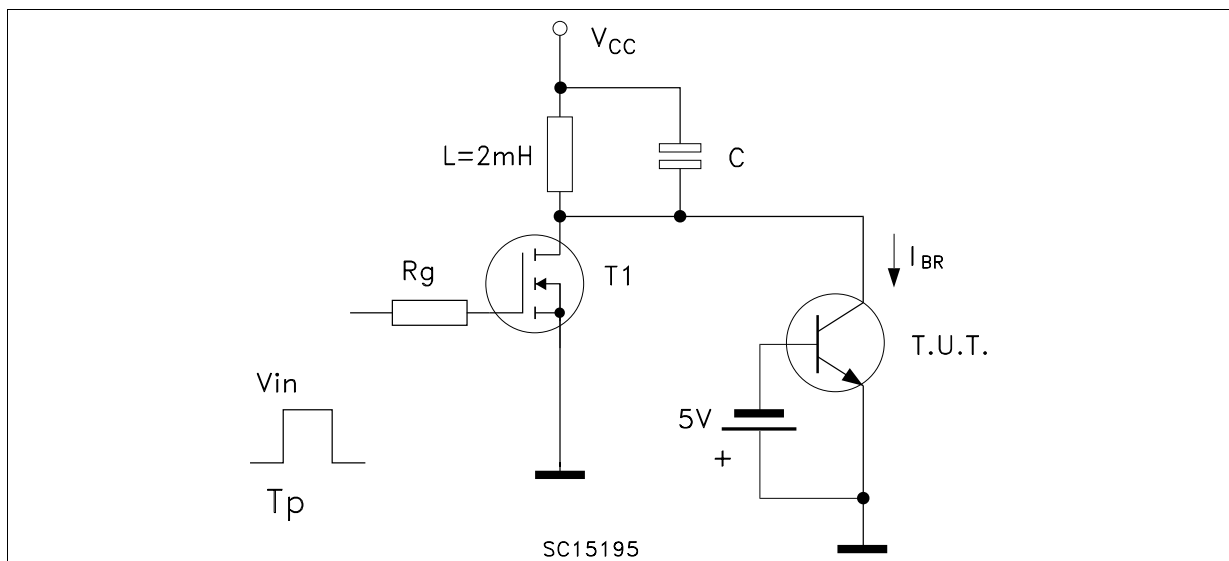


Resistive Load Switching Times



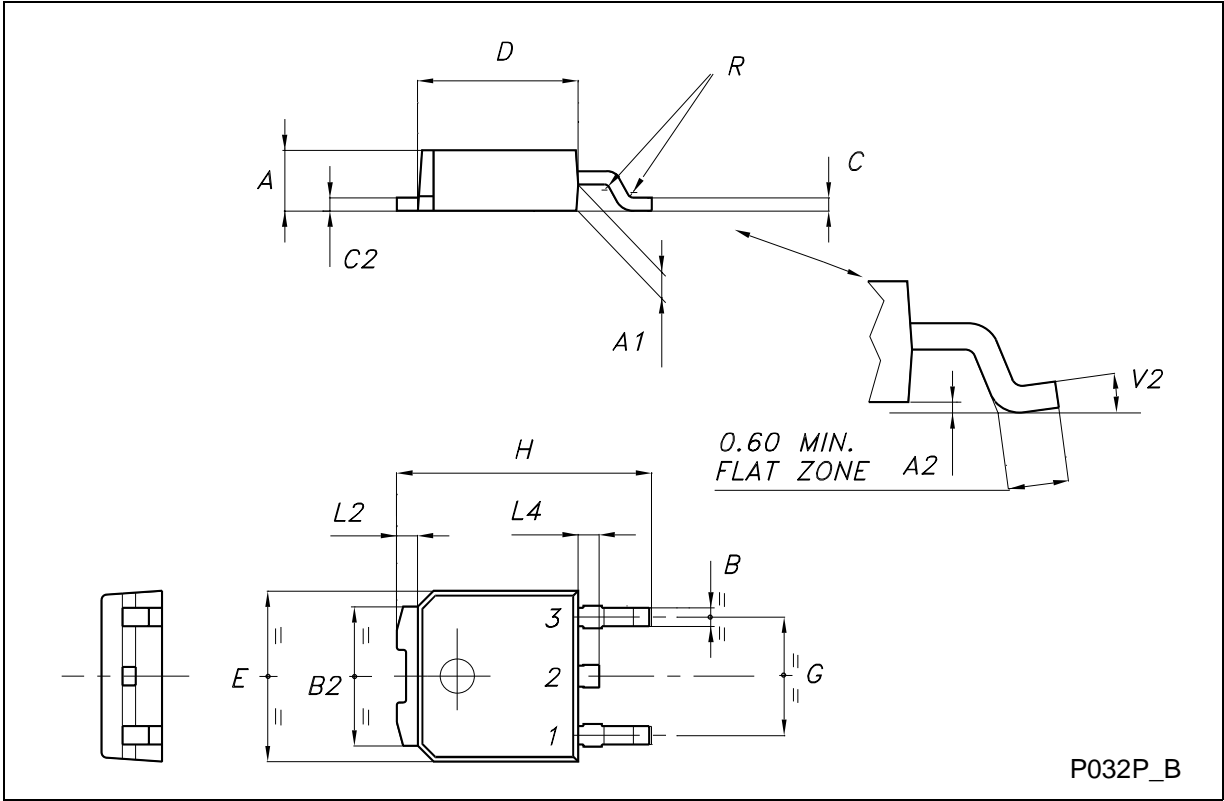
Reverse Biased Safe Operating Area



**Figure 1: Resistive Load Switching Test Circuit****Figure 2: Energy Rating Test Circuit**

TO-252 (DPAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.20		2.40	0.087		0.094
A1	0.90		1.10	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.90	0.025		0.035
B2	5.20		5.40	0.204		0.213
C	0.45		0.60	0.018		0.024
C2	0.48		0.60	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.60	0.252		0.260
G	4.40		4.60	0.173		0.181
H	9.35		10.10	0.368		0.398
L2		0.8			0.031	
L4	0.60		1.00	0.024		0.039
V2	0°		8°	0°		0°



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